

# PATENT ABSTRACTS OF JAPAN

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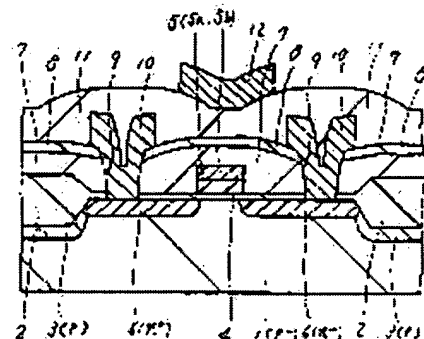
## (54) SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE

### (57)Abstract:

**PURPOSE:** To prevent a first insulating film from being reflowed again by means of a second insulating film, by providing an interlayer insulating film consisting of a first insulating film which is reflowed at a predetermined temperature and a second insulating film superposed on the first film and not reflowed at said temperature.

**CONSTITUTION:** An MISFET is constituted by a semiconductor substrate 1 provided with a field insulating film 2, a channel stopper region 3, a gate insulation film 4, a gate electrode 5 and source/drain 6. A

BPSG film (first insulation film) 7 is reflowed on the substrate 1, a second insulating film 8 of silicon oxide is reflowed on the film 7, a patterned interconnection layer 10 is reflowed on the film 8 and a BPSG film (third insulation film) 11 is reflowed thereon. In this manner, the film 7 is prevented from being reflowed again during reflowing of the film 11 by the presence of the film 8 which is not reflowed at the reflowing temperature of the film 11. Thus, no disconnection is caused in the interconnection 10.



## LEGAL STATUS

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